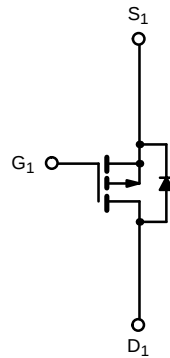
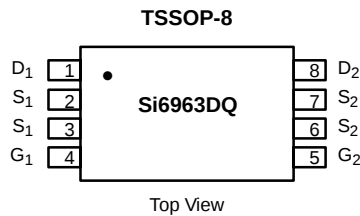


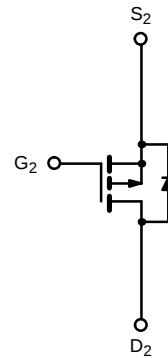


Dual P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.050 @ $V_{GS} = -4.5$ V	-3.5
	0.085 @ $V_{GS} = -2.5$ V	-2.7

TrenchFET[®]
Power MOSFETs
2.5-V Rated

P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	10 sec	Steady State
Drain-Source Voltage		V_{DS}	-20	
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	-3.5	-3.0
	$T_A = 70^\circ\text{C}$		-2.8	-2.5
Pulsed Drain Current		I_{DM}	-30	
Continuous Source Current (Diode Conduction) ^a		I_S	-1.25	-0.7
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	1.14	0.83
	$T_A = 70^\circ\text{C}$		0.73	0.53
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	86	110	$^\circ\text{C/W}$
	Steady State		124	150	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	52	165	

Notes

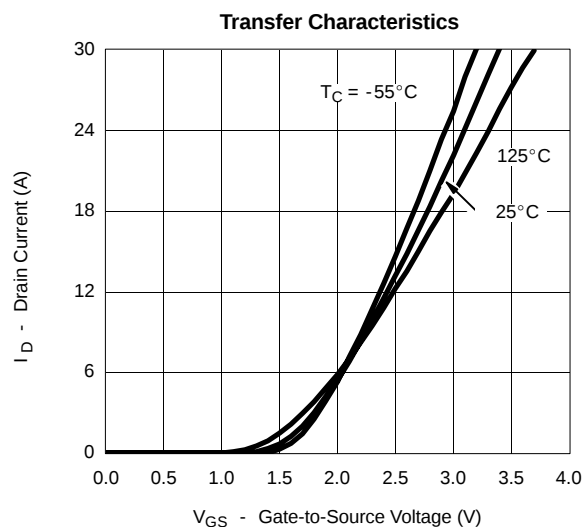
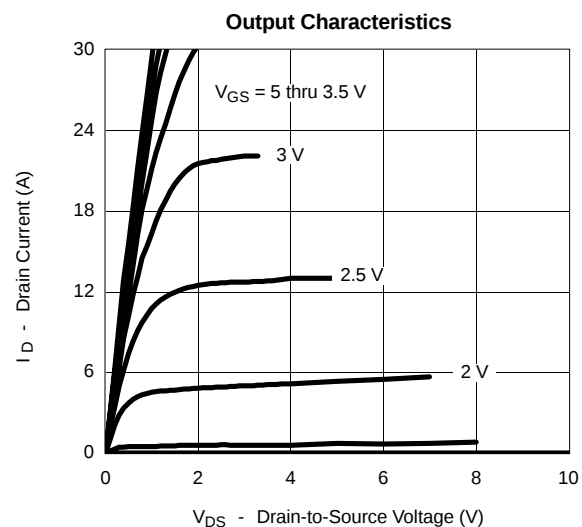
a. Surface Mounted on FR4 Board.

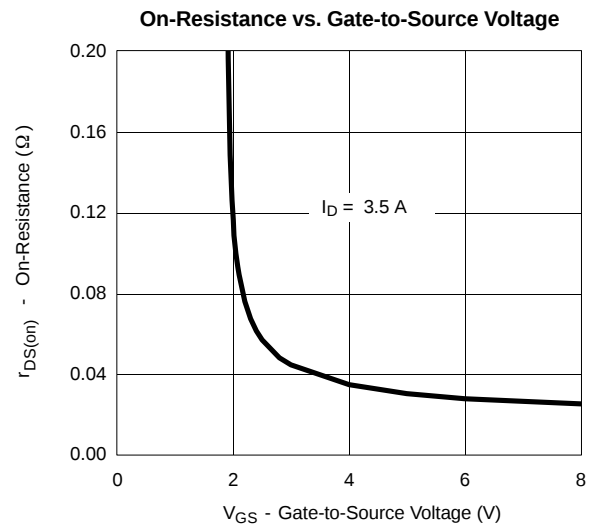
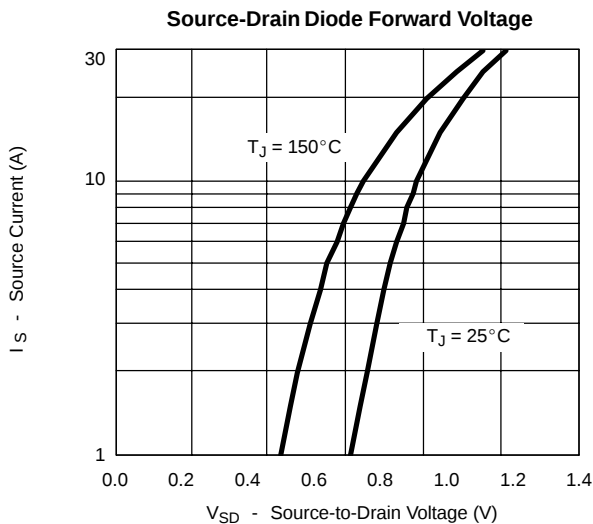
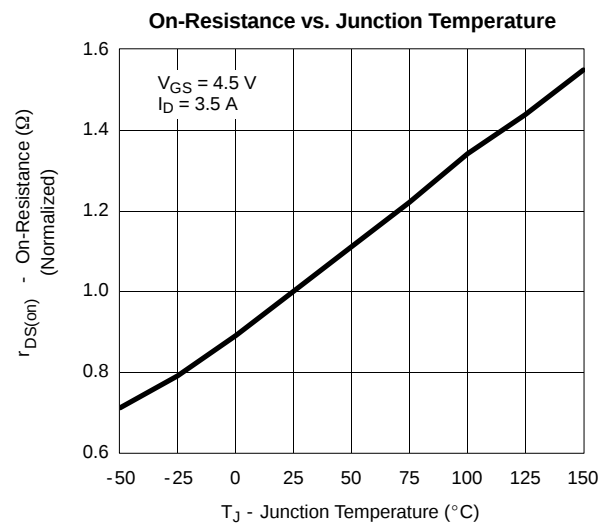
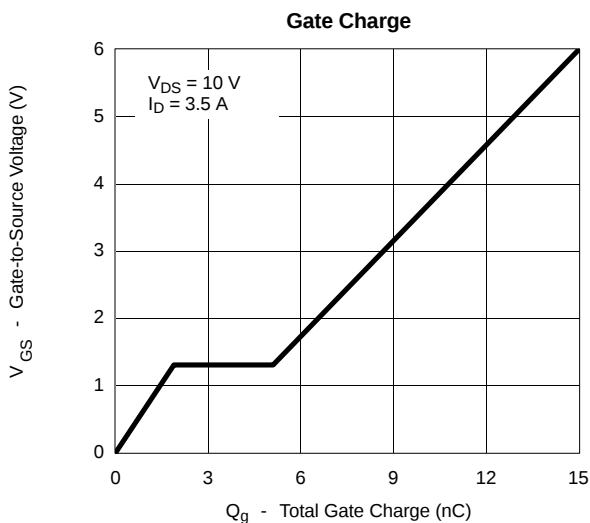
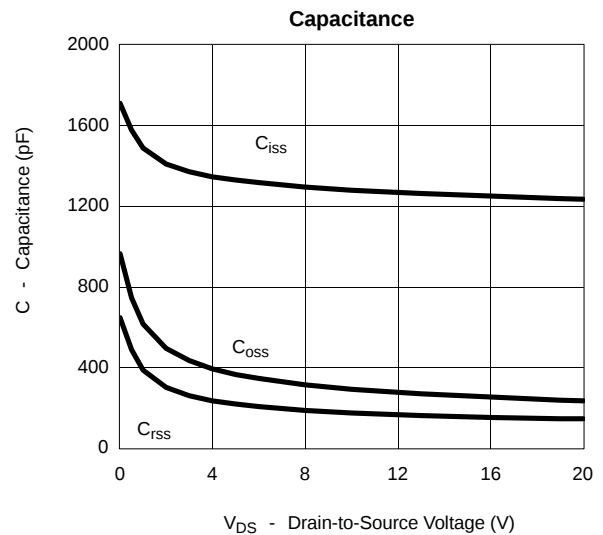
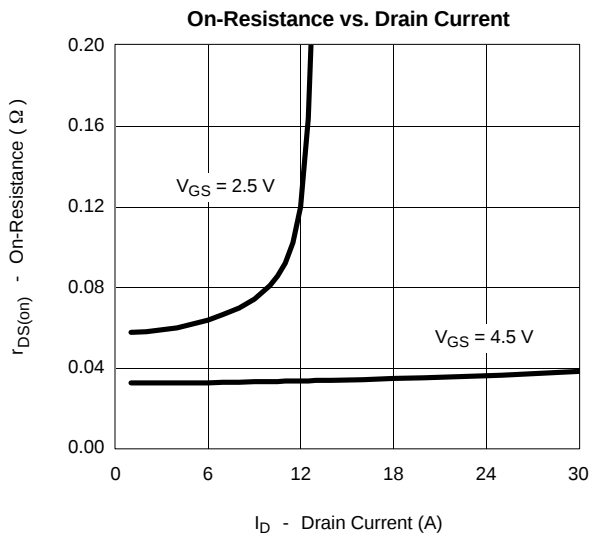
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	-0.6		-1.4	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 12\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -20\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			-25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -5\ \text{V}$, $V_{GS} = -4.5\ \text{V}$	-30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}$, $I_D = -3.5\ \text{A}$		0.037	0.050	Ω
		$V_{GS} = -2.5\ \text{V}$, $I_D = -2.7\ \text{A}$		0.062	0.085	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}$, $I_D = -3.5\ \text{A}$		10		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.25\ \text{A}$, $V_{GS} = 0\ \text{V}$		-0.72	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\ \text{V}$, $V_{GS} = -4.5\ \text{V}$, $I_D = -3.5\ \text{A}$		12.5	20	nC
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			3.2		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\ \text{V}$, $R_L = 10\ \Omega$ $I_D \cong -1\ \text{A}$, $V_{GEN} = -4.5\ \text{V}$, $R_G = 6\ \Omega$		20	30	ns
Rise Time	t_r			26	40	
Turn-Off Delay Time	$t_{d(off)}$			48	75	
Fall Time	t_f			30	45	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.25\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		30	50	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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